

ABSOLUTE MAXIMUM RATINGS AT T_A=25°C

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	60	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	75	mW
IR Diode Peak Forward Current (Pulse Wide = 10 μ S, 300 pps)	1	A
Diode Power Dissipation	100	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25°C to + 85°C	
Storage Temperature Range	-40°C to + 100°C	
Lead Soldering Temperature [1.6mm(.063") From Case]	260°C for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT $T_A=25^{\circ}\text{C}$

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED							
Forward Voltage		V_F		1.2	1.6	V	$I_F = 20\text{mA}$
Reverse Current		I_R			100	μA	$V_R=5\text{V}$
OUTPUT PHOTOTRANSISTOR							
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	30			V	$I_C=1\text{mA}$
Emitter-Collector Breakdown Voltage		$V_{(BR)ECO}$	5			V	$I_E=100\mu\text{A}$
Collector-Emitter Dark Current		I_{CEO}			100	nA	$V_{CE}=10\text{V}$
COUPLER							
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$			0.4	V	$I_C=0.25\text{mA}$ $I_F=20\text{mA}$
On State Collector Current		$I_{c(ON)}$	0.5			mA	$V_{CE}=5\text{V}$ $I_F=20\text{mA}$
Response Time	Rise Time	t_r		3	15	μS	$V_{CE}=5\text{V}, I_c=2\text{mA}$ $R_L=100\Omega$
	Fall Time	t_f		4	20		

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

Fig.1 Power Dissipation vs. Ambient Temperature

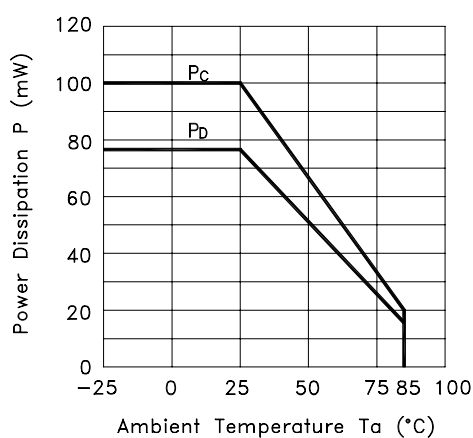


Fig.2 Forward Current vs. Forward Voltage

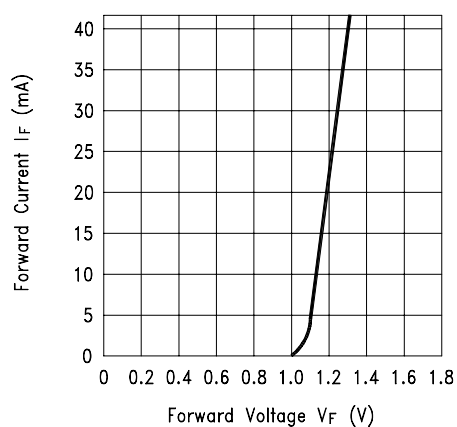


Fig.3 Collector Current vs. Collector-emitter Voltage

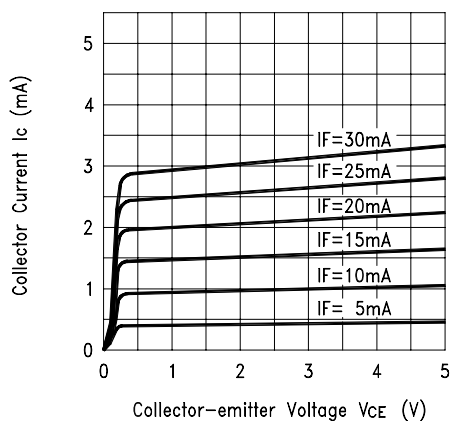
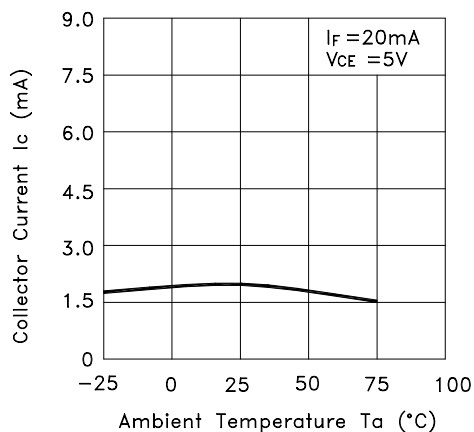


Fig.4 Collector Current vs. Ambient Temperature



TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

Fig.5 Collector-emitter Saturation Voltage vs. Ambient Temperature

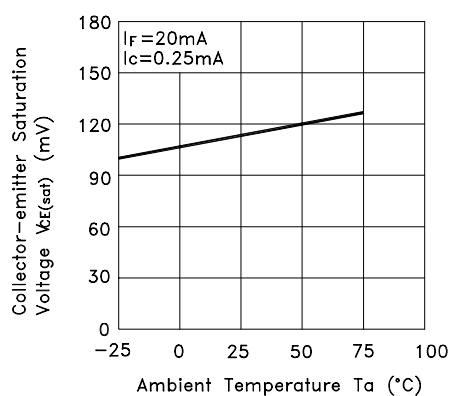
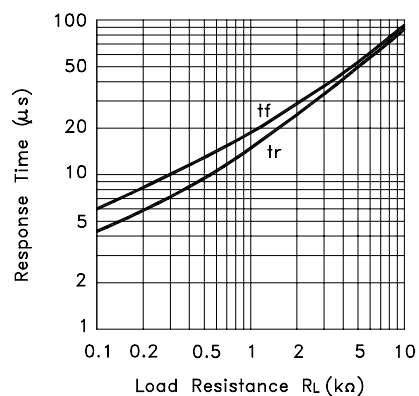


Fig.6 Response Time vs. Load Resistance



Test Circuit for Response Time

